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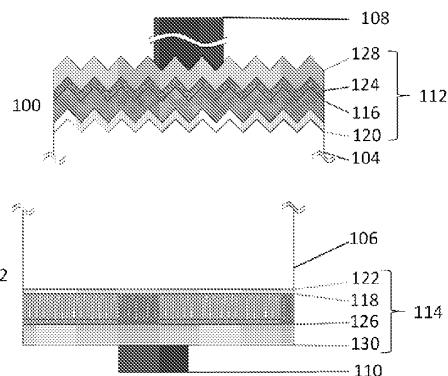


Figure 1

(57) Abstract: Disclosed is a multi-layer contact structure comprising a semiconductor substrate, a terminal electrode, and a contact layer structure. The contact layer structure comprises a metal-containing carrier selective (MCS) layer, the contact layer structure being in intimate contact with the semiconductor substrate and the terminal electrode.

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